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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	20MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	10
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 7x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-SSOP (0.173", 4.40mm Width)
Supplier Device Package	16-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10y47asp-50

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

O ROM, RAM capacities

Flash ROM	RAM	10 pins	16 pins
4 KB	512 B	-	R5F10Y47ASP Note 2
2 KB	256 B	R5F10Y16ASP	R5F10Y46ASP Note 2
1 KB	128 B	R5F10Y14ASP	R5F10Y44ASP Note 2

Notes 1. 16-pin products only

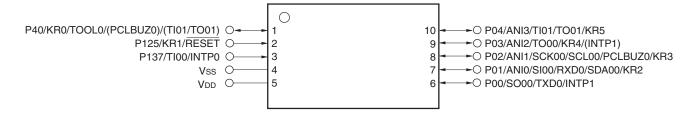
2. Under development

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

1.3 Pin Configuration (Top View)

1.3.1 10-pin products

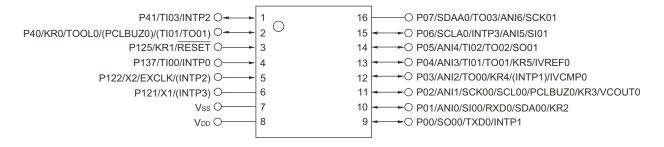
• 10-pin plastic LSSOP (4.4 × 3.6)



- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.2 16-pin products

• 16-pin plastic SSOP (4.4 × 5.0)



- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.4 Pin Identification

ANI0 to ANI6 : Analog Input

INTP0 to INTP3 : External Interrupt Input

 KR0 to KR5
 : Key Return

 P00 to P07
 : Port 0

 P40, P41
 : Port 4

 P121, P122, P125
 : Port 12

 P137
 : Port 13

PCLBUZ0 : Programmable Clock Output/ Buzzer Output

EXCLK : External Clock Input
X1, X2 : Crystal Oscillator
IVCMP0 : Comparator Input
VCOUT0 : Comparator Output

IVREF0 : Comparator Reference Input

RESET : Reset

RxD0 : Receive Data

SCK00, SCK01 : Serial Clock Input/Output
SCL00, SCLA0 : Serial Clock Output
SDA00, SDAA0 : Serial Data Input/Output
SI00, SI01 : Serial Data Input
SO00, SO01 : Serial Data Output

TI00 to TI03 : Timer Input
TO00 to TO03 : Timer Output

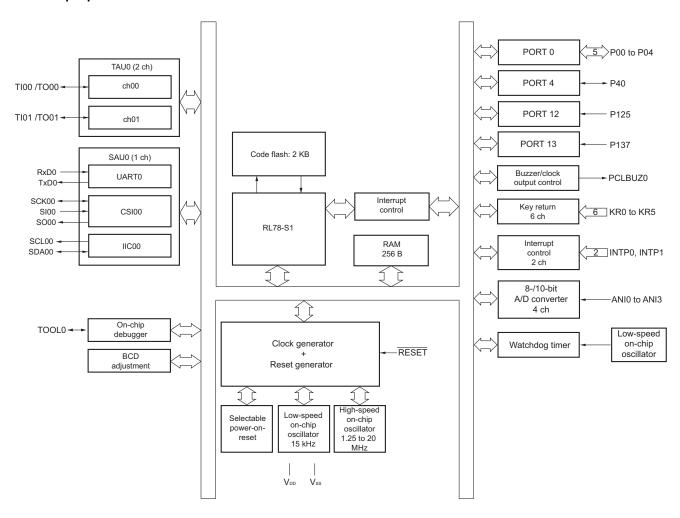
TOOL0 : Data Input/Output for Tool

TxD0 : Transmit Data
Vdd : Power Supply
Vss : Ground

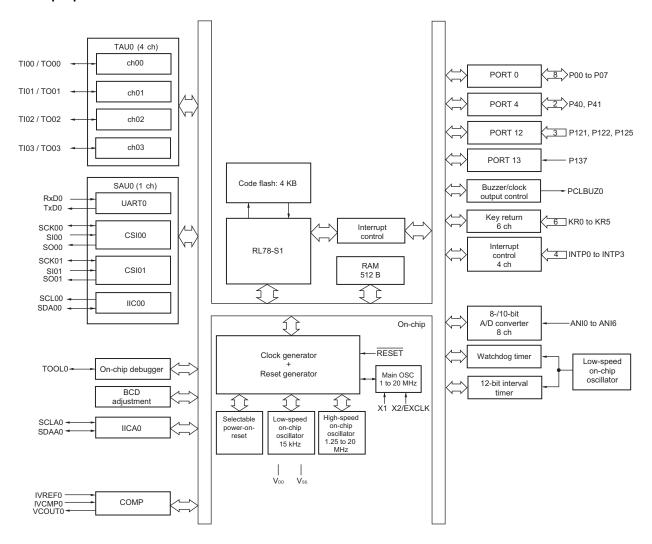


1.5 Block Diagram

1.5.1 10-pin products



1.5.2 16-pin products



1.6 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

i	Item	10-	-pin	16-pin			
		R5F10Y16ASP	R5F10Y14ASP	R5F10Y47ASP	R5F10Y46ASP	R5F10Y44ASP	
Code flash m	emory	2 KB	1 KB	4 KB	2 KB	1 KB	
RAM		256 B	128 B	512 B	256 B	128 B	
	High-speed system clock	_		, ,			
	High-speed on-chip	• 1.25 to 20 MHz (VDD	= 2.7 to 5.5 V)	1			
	oscillator clock	• 1.25 to 5 MHz (VDD = 2.0 to 5.5 V)					
Low-speed or clock	n-chip oscillator	15 kHz (TYP)					
General-purp	ose register	8-bit register × 8					
Minimum inst time	truction execution	0.05 μs (20 MHz operation)					
Instruction se	et	Data transfer (8 bits)					
		Adder and subtractor	r/logical operation (8 bits)			
		Multiplication (8 bits:	× 8 bits)				
		Rotate, barrel shift, and bit manipulation (set, reset, test, and Boolean operation), etc.					
I/O port	Total	8		14			
	CMOS I/O	6 (N-ch open-drain out	out (VDD tolerance): 2)	10 (N-ch open-drain output (VDD tolerance): 4)			
	CMOS input	2		4			
Timer	16-bit timer	2 channels		4 channels			
	Watchdog timer	1 channel		Ţ			
	12-bit interval timer	_		1 channel			
	Timer output	2 channels (PWM outp	ut: 1)	4 channels (PW	/M outputs: 3 ^{Note 1})		
Clock output/	buzzer output	1					
		2.44 kHz to 10 MHz: (P	eripheral hardware clock		operation)		
Comparator		_		1			
8-/10-bit reso	olution A/D converter	4 channels		8 channels			
Serial interfac	ce		1 channel/simplified I ² C: 2 channels/simplified I ² C:				
	I ² C bus	_		1 channel			
Vectored	Internal	8		14			
interrupt sources	External	3		5			
Key interrupt		6					
Reset			chdog timer				
Selectable po	ower-on-reset circuit	Detection voltage: 2.0 \	//2.4 V/2.7 V/4.0 V				
On-chip debu	ug function	Provided					
Power supply	voltage	V _{DD} = 2.0 to 5.5 V					
Operating arr	nbient temperature	Ta = - 40 to + 85 °C					

Notes 1. The number of outputs varies, depending on the setting of channels in use and the number of the master (see 6.8.3 Operation as multiple PWM output function in the RL78/G10 User's Manual).

2. The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

- Cautions 1. This chapter explains the electrical specifications of two products, the R5F10Y16ASP and the R5F10Y14ASP.
 - 2. Electrical specifications for the 16-pin products are T. B. D. because these products are under development.
 - 3. The RL78/G10 has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 4. The pins mounted depend on the product. Refer to 2.1 Port Functions and 2.2.1 Functions for each product in the RL78/G10 User's Manual.

2.1 Absolute Maximum Ratings

$(T_A = 25^{\circ}C)$

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V _{DD}			-0.5 to +6.5	V
Input Voltage	Vıı			-0.3 to V _{DD} + 0.3 ^{Note}	V
Output Voltage	V _{O1}			-0.3 to V _{DD} + 0.3	V
Output current, high	І он1	Per pin		-40	mA
		Total of all pins	P40	-40	mA
		-140 mA	P00 to P04	-100	mA
Output current, low	lo _{L1}	Per pin	·	40	mA
		Total of all pins	P40	40	mA
		140 mA	P00 to P04	100	mA
Operating ambient temperature	TA			-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C

Note Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. The reference voltage is Vss.

2.2 Oscillator Characteristics

2.2.1 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator oscillation clock frequency Notes 1, 2	fін		1.25		20	MHz
High-speed on-chip oscillator oscillation		Ta = -20 to +85°C	-2.0		+2.0	%
clock frequency accuracy		Ta = -40 to -20°C	-3.0		+3.0	%
Low-speed on-chip oscillator oscillation clock frequency Note 3	fıL			15		kHz
Low-speed on-chip oscillator oscillation clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 2 of option byte (000C2H).

- 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.
- 3. This only indicates the oscillator characteristics.



- Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

- Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80 % and loL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- **4.** Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- 5. The value under the condition which satisfies the high-level output current (IOH1).
- 6. The value under the condition which satisfies the low-level output current (IoL1).
- Cautions 1. P00 and P01 do not output high level in N-ch open-drain mode.
 - 2. The maximum value of ViH of P00 and P01 is VDD even in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.



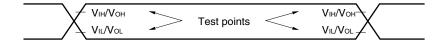
2.4 AC Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

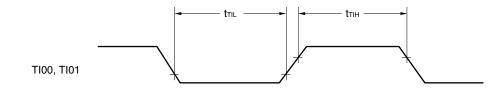
Items	Symbol	Condit	tions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main system clock	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.05		0.8	μs
instruction execution time)		(fmain) operation	$2.0~V \leq V_{DD} \leq 5.5~V$	0.2		0.8	μs
TI00, TI01 input high-level width, low-level width	tπн, tπ∟	Noise filter is not used		1/fмск + 10			ns
TO00, TO01 output frequency	fто	$4.0~V \leq V_{DD} \leq 5.5~V$				10	MHz
		$2.7~V \leq V_{DD} < 4.0~V$				5	MHz
		$2.0~V \leq V_{DD} < 2.7~V$				2.5	MHz
PCLBUZ0 output frequency	fpcL	$4.0~V \leq V_{DD} \leq 5.5~V$				10	MHz
		$2.7~V \leq V_{DD} < 4.0~V$				5	MHz
		$2.0~V \leq V_{DD} < 2.7~V$				2.5	MHz
RESET low-level width	t RSL			10			μs

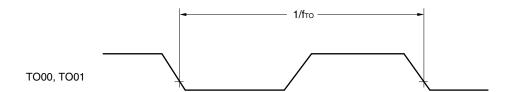
Remark fmck: Timer array unit operation clock frequency

AC Timing Test Points



TI/TO Timing





2.5 Serial Communication Characteristics

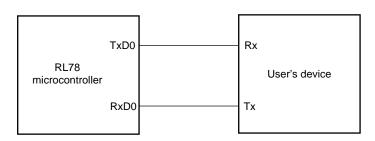
2.5.1 Serial array unit

(1) UART mode

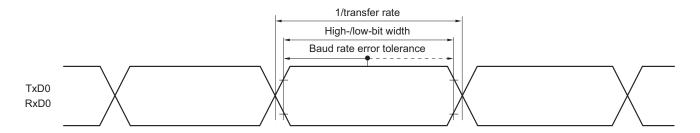
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

,						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					fмск/6	bps
		Theoretical value of the maximum transfer rate fclk = fMCK = 20 MHz			3.3	Mbps

UART mode connection diagram



UART mode bit width (reference)



Remark fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00))



(3) CSI mode (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

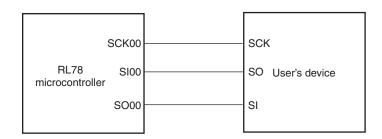
Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	fмск = 20 MHz	8/fмск			ns
			fмcк ≤ 10 MHz	6/ƒмск			ns
		$2.0~V \leq V_{DD} < 2.7~V$		6/ƒмск			ns
SCKp high-/low-level width	tкн2,	$2.0~V \leq V_{DD} \leq 5.5~V$		tkcy2/2			ns
	t _{KL2}						
SIp setup time (to SCKp↑) ^{Note 1}	tsık2	$2.7~\text{V} \le \text{V}_{\text{DD}} \le 5.5~\text{V}$		1/fмcк+ 20			ns
		$2.0~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$		1/fмск+ 30			ns
SIp hold time (from SCKp [↑]) Note 2	tksi2	$2.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		1/fмск+ 31			ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4	2.7 V ≤ V _{DD} ≤ 5.5 V			2/fмcк+50	ns
			$2.0 \text{ V} \le \text{V}_{DD} < 2.7$ V			2/fмcк+ 110	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.

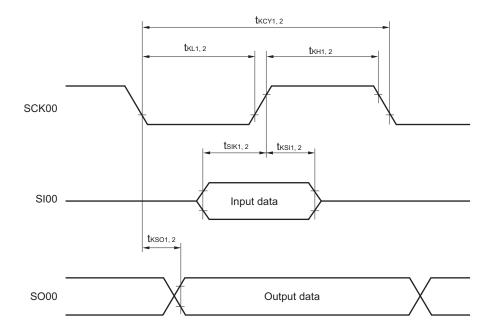
Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0)

2. fmcx: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

CSI mode connection diagram



CSI mode serial transfer timing $\label{eq:csi} \mbox{(When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1.)}$



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

(Target ANI pin : ANI0 to ANI3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	V _{DD} = 5 V		±1.7	±3.1 Note 2	LSB
			V _{DD} = 3 V		±2.3	±4.5 Note 2	LSB
Conversion time	tconv	10-bit resolution	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.4		18.4	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	4.6		18.4	μs
Zero-scale error ^{Note 1}	Ezs	10-bit resolution	V _{DD} = 5 V			±0.19 Note 2	%FSR
			V _{DD} = 3 V			±0.39 Note 2	%FSR
Full-scale error ^{Note 1}	Ers	10-bit resolution	V _{DD} = 5 V			±0.29 Note 2	%FSR
			V _{DD} = 3 V			±0.42 Note 2	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	V _{DD} = 5 V			±1.8 Note 2	LSB
			V _{DD} = 3 V			±1.7 Note 2	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	V _{DD} = 5 V			±1.4 Note 2	LSB
			V _{DD} = 3 V			±1.5 Note 2	LSB
Analog input voltage	VAIN			0		V _{DD}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This is the characteristic evaluation value plus or minus 3. These values are not used in the shipping inspection.

2.6.2 SPOR circuit characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VSPOR0	Power supply rise time	4.08	4.28	4.45	V
		Power supply fall time	4.00	4.20	4.37	٧
	V _{SPOR1}	Power supply rise time	2.76	2.90	3.02	٧
		Power supply fall time	2.70	2.84	2.96	٧
	VSPOR2	Power supply rise time	2.44	2.57	2.68	٧
		Power supply fall time	2.40	2.52	2.62	٧
	V _{SPOR3}	Power supply rise time	2.05	2.16	2.25	٧
		Power supply fall time	2.00	2.11	2.20	٧
Minimum pulse width Note	Tspw		300			μs

Note Time required for the reset operation by the SPOR when VDD becomes under VSPDR.

2.6.3 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms



2.6.4 Data retention power supply voltage characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention power supply voltage	VDDDR		1.9		5.5	V
range						

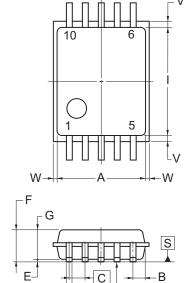
Caution Data is retained until the power supply voltage becomes under the minimum value of the data retention power supply voltage range. Note that data in the RAM and RESF registers might not be cleared even if the power supply voltage becomes under the minimum value of the data retention power supply voltage range.

3. PACKAGE DRAWINGS

3.1 10-pin products

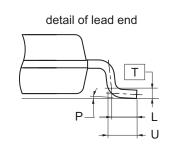
R5F10Y16ASP, R5F10Y14ASP

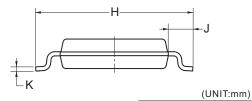
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05



 \triangle N S

 \vdash D \oplus M M





NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

	(
ITEM	DIMENSIONS	
Α	3.60±0.10	
В	0.50	
С	0.65 (T.P.)	
D	0.24 ± 0.08	
E	0.10 ± 0.05	
F	1.45 MAX.	
G	1.20 ± 0.10	
Н	6.40 ± 0.20	
I	4.40 ± 0.10	
J	1.00 ± 0.20	
K	$0.17^{+0.08}_{-0.07}$	
L	0.50	
М	0.13	
N	0.10	
Р	3° +5°	
Т	0.25 (T.P.)	
U	0.60 ± 0.15	
V	0.25 MAX.	
W	0.15 MAX.	

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Revision History	RL78/G10 Data Sheet
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		Description		
Rev.	Date	Page	Summary	
1.00	Apr 15, 2013	-	First Edition issued	

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

Notice

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